AW318C Datasheet

Zhuhai Jieli Technology Co.,LTD

Version 1.1

Date 2024.07.04

Copyright © Zhuhai Jieli Technology Co.,LTD. All rights reserved.



Revision History

Date	Revision	Description
2024.04.12	V1.0	Initial Release
2024.07.04	V1.1	Update IC Marking Information





Table of Contents

Re	vision History		1
Та	ble of Contents		2
A۷	V318C Features		3
1	Block Diagram		4
2	Pin Definition		5
	2.1 Pin Assignment		5
	2.2 Pin Description		6
3			
	3.1 Absolute Maximum Ratings		7
	3.2 ESD Ratings		7
	3.3 PMU Characteristics		7
	3.5 BT Characteristics		9
4	Package Information	<u> </u>	10
5	IC Marking Information		11
6	Solder-Reflow Condition		12



AW318C Features

SYSTEM

- > 32bit CPU 160MHz
- ➤ Support MATH/AES128
- I-cache
- Support EMU
- On-chip SRAM 32kbyte
- Support MPU
- Support UDMA
- Built-In Flash
- ➤ 24MHz crystal oscillator
- > Internal low jitter low power RC oscillator
- Internal PLL

Bluetooth

- BLE5.4 +2.4GHz-Proprietary (QDID 223418)
- Support AoA Transmitter
- Support long range BLE
- Maximum transmitting power 8dBm
- Receiver sensitivity
 - ❖ -96dBm @BLE-1Mbps
 - ◆ -93dBm @BLE-2Mbps
 - ◆ -98dBm @BLE-S2

Peripherals

- 1 x Full speed USB
- 4 x Multi-function 32bit timer
- ➤ 1 x IR RX/TX
- 2 x UART interface
- 1 x I²C Master/Slave interface
- 2 x SPI Master/Slave interface
- ➤ 1 x QDEC
- ➤ 4 x MCPWM
- ➤ 2 x LEDC
- 1 x 10bit ADC(3 Channel)
- 3 x GPIO Support function remapping

PMU

- Support temperature sensor
- ➤ VPWR range 2.7V to 5.5V
- ➤ IOVDD range 1.8V to 3.6V
- > Deep sleep mode (IOVDD @3.0V)
 - 170nA (External wakeup)
 - 1.37uA (32kHz RC OSC+wakeup)
 - 2.9uA (32kHz RC OSC+wakeup+16k retention SRAM)

Packages

➤ SOP8

Temperature

- Operating temperature
 - TC = -20° C to $+85^{\circ}$ C (standard range)
 - $TC = -40^{\circ}C$ to $+105^{\circ}C$ (extended range)
- Storage temperature -65°C to +150°C

Applications

- Mouse devices
- Non-audio remote controller
- Selfie stick
- Page turner
- Adaptive USB
- Bluetooth moudle
- Price tag and other diversified IOT product



1 Block Diagram

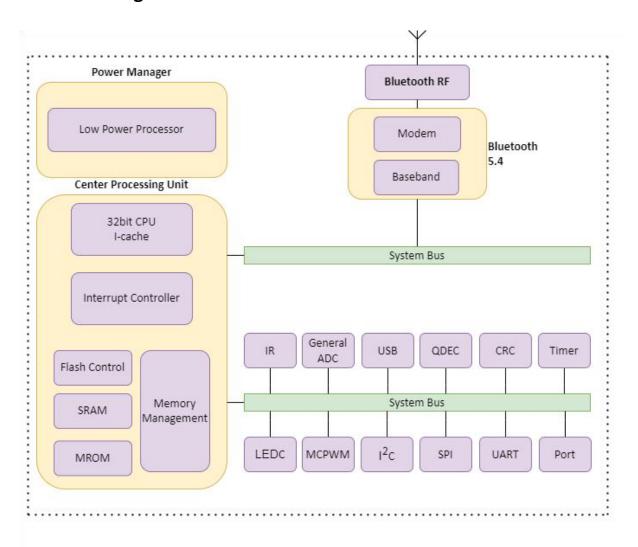


Figure 1-1 AW318C Block Diagram



2 Pin Definition

2.1 Pin Assignment

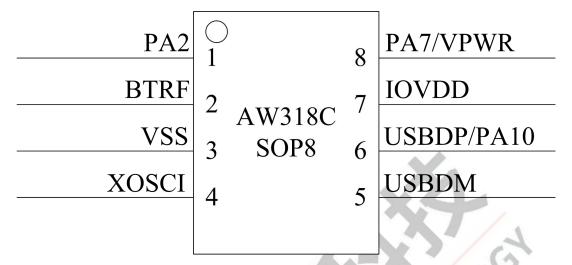


Figure 2-1 AW318C Pin Assignment



2.2 Pin Description

Table 2-2-1 AW318C Pin Description

Pin No.	Name	Туре	IO Initial State	Description
1	PA2	1/0	7	ADC2(ADC Input Channel 2)
1	PAZ	1/0	Z	SPIO_DOB(0)
2	BTRF	RF		Bluetooth RF Antenna
3	VSS	G		Ground
4	XOSCI	1		Crystal Oscillator Input
5	USBDM	1/0	15kΩ Pull-down	ADC13(ADC Input Channel 13)
	USBDP	1/0	15kΩ Pull-down	ADC14(ADC Input Channel 14)
6	PA10	1/0	Z	ADC10(ADC Input Channel 10)
7	IOVDD	Р		IO Power
8	VPWR	Р		Battery Input
٥	PA7	I/O	Z	- 25-7

Note

- 1.IO initial state abbreviations Z--High resistance, H--High level, L--Low level, X--May be changed during power on.
- 2.Timer, IR, MCPWM, QDEC, UART, LEDC, I²C, SPI1 functions can be remapped to any I/O.

Table 2-2-2 Pin Types Description

Pin Type	Description	Pin Type	Description
Р	Power	1/0	Input or Output
G	Ground	9	Input
RF	RF antenna	0	Output



3 Electrical Characteristics

3.1 Absolute Maximum Ratings

Table 3-1 Absolute Maximum Ratings

Symbol	Parameter	Min	Max	Unit
Topt	Operating temperature	-20	+85	$^{\circ}$
Tstg	Storage temperature	-65	+150	$^{\circ}$
VPWR	Complex Veltage	-0.3	6.0	V
IOVDD	Supply Voltage	-0.3	3.6	V
GPIO	Input voltage of GPIO (except PA7)	-0.3	3.6	V
HVTIO	Input voltage of HVT-IO (PA7)	-0.3	6.0	V

Note

3.2 ESD Ratings

Table 3-2 ESD Ratings

Parameter	Тур	Test pin	Reference standard
Human Body Mode	±8kV	All pins	JEDEC EIA/JESD22-A114
Machine Mode	±400V	All pins	JEDEC EIA/JESD22-A115
Charge Device Model	±2kV	All pins	ANSI/ESDA/JEDEC JS-002-2022

3.3 PMU Characteristics

Table 3-3-1 PMU Characteristics under VPWR supply

	Table 5 1 : We district the area of the supply					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
VPWR	Power supply	-	2.7		5.5	٧
Operating mo	Operating mode					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
IOVDD	Voltage ou <mark>tput</mark>			3.0		V
טטעטו	Loading current	IOVDD=3.0V@VPWR = 3.7V			60	mA
Low Power me	Low Power mode					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
IOVDD	Loading current	IOVDD=3.0V@VPWR = 3.7V			8	mA

Table 3-3-2 PMU Characteristics under IOVDD supply

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
IOVDD	Power supply	-	1.8		3.6	V

^{1.}Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device.



3.4 IO Characteristics

Table 3-4 IO Characteristics

Input Cha	racteristics					
Symbol	Parameter	Conditions	10	Min	Max	Unit
V _{IL}	Low-Level Input Voltage	IOVDD = 3.0V	PA2,PA7,PA10	-0.3	1.4	V
			PA2,PA10			
V	18.1.1. 11	IOVDD = 3.0V	USBDP	1.7	3.3	V
V_{IH}	High-Level Input Voltage		USBDM			
		IOVDD = 3.0V	PA7	1.7	5.5	V
Output Ch	aracteristics					
Symbol	Parameter	Conditions	10	Т	ур	Unit
I _{OL}	Output Current	IOVDD = 3.0V Voutput = 0.3V	PA2,PA10	9(H 21(F	D=0) D=1) HD=2) HD=3)	mA
		IOVDD = 3.0V Voutput = 0.3V	PA7 USBDP USBDM	01.8		mA
І _{он}	Output Current	IOVDD = 3.0V Voutput = 2.7V	PA2,PA10	3(HD=0) 9(HD=1) 21(HD=2) 54(HD=3)		mA
		IOVDD = 3.0V Voutput = 2.7V	PA7 USBDP USBDM	8		mA
Internal R	esistance Characteristics					
Symbol	Parameter	Conditions	10	Т	ур	Unit
R_pu	Pull-up Resistance	IOVDD = 3.0V	PA2,PA7,PA10	100k(PU=1) (PU=2) PU=3)	Ω
•		IOVDD = 3.0V	USBDP		.5k	Ω
		IOVDD = 3.0V	USBDM	18	30k	Ω
R_{pd}	Pull-down Resistance	IOVDD = 3.0V	PA2,PA7,PA10	100k(PD=1) (PD=2) PD=3)	Ω
		IOVDD = 3.0V	USBDP USBDM	15k		Ω

Note

1.Internal pull-up/pull-down resistance accuracy ±20%.



3.5 BT Characteristics

3.5.1 Transmitter

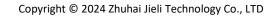
Table 3-5-1 Transmitter characteristics

Parameter	Conditions	Min	Тур	Max	Unit
Maximum RF Transmit Power	BLE-1Mbps		7	8	dBm

3.5.2 Receiver

Table 3-5-2 Receiver characteristics

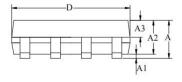
Parameter	Conditions	Min	Тур	Max	Unit
Sensitivity	BLE-1Mbps		-96		dBm
	BLE-2Mbps	/	-93		dBm
	BLE-S2	\	-98		dBm
	BLE-S8	-	-103	//	dBm

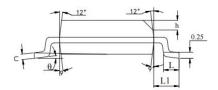


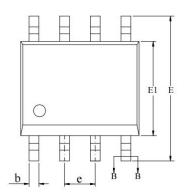


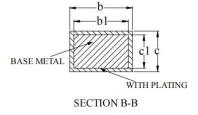
4 Package Information

4.1 SOP8









MILLIMETER SYMBOL NOM MAX MIN A 1.75 0.225 A1 0.10 1.30 1.50 A2 0.70 A3 0.60 0.39 0.47 b bl 0.38 0.44 0.41 0.20 0.24 0.19 0.20 0.21 c1 D 4.80 5.00 E 5.80 6.20 El 3.80 4.00 3.90 e 1.27BSC 0.50 h 0.25 0.50 0.80 L Ll 8° θ 0

Figure 4-1 AW318C Package



5 IC Marking Information

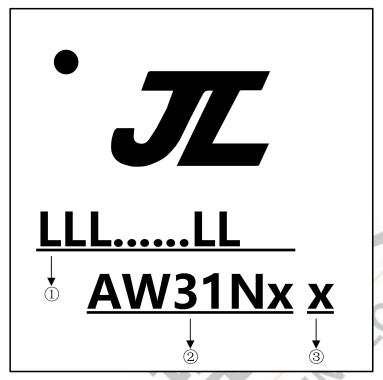


Figure 5-1 AW318C Package Outline

- 1 LLL.....LL LOT No. , It contains 7 to 18 alphanumerics
- 2 AW31Nx Chip Model
- (3) x Built-in flash size
 - 0 No Flash Memory
 - 2 2Mbit Flash
 - 4 4Mbit Flash



6 Solder-Reflow Condition

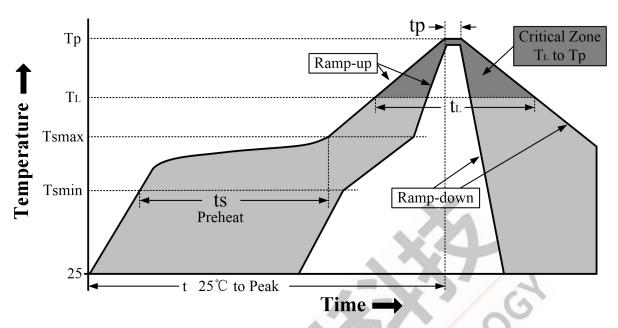


Figure 6-1 Classification Reflow Profile

Table 6-1 Classification Profiles

	Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly	
	Temperature Min (T _{smin})	100℃	150℃	
Preheat/Soak	Temperature Max (T _{smax})	150°C	200℃	
	Time (ts) from (T _{smin} to T _{smax})	60-120 seconds	60-180 seconds	
Average ramp-	up rate (T _{smax} to T _p)	3℃/second max	3℃/second max	
Liquidus temperature (T _L)		183℃	217℃	
Time (t _L) maint	ained above T _L	60-150 seconds	60-150 seconds	
Peak package b	ood <mark>y temperature (T_p)</mark>	See Table 6-2	See Table 6-3	
Time within 5°0	C of actual	10-30 seconds	20-40 seconds	
Peak Temperature (tp) ²		10-30 Seconds	20-40 seconds	
Ramp-down rate (Tp to TL)		6°C/second max	6°C/second max	
Time 25℃ to p	eak temperature	6 minutes max	8 minutes max	

Note

- 1.All temperatures refer to topside of the package, measured on the package body surface
- 2.Time within 5 $^{\circ}$ C of actual peak temperature (tp) specified for the reflow profiles is a "supplier" and "user" maximum.

Table 6-2 SnPb Classification Temperature

Package	Volume mm ³	Volume mm³ ≥ 350	
Thickness	< 350		
<2.5 mm	240 +0/-5℃	225 +0/-5°C	
≥2.5 mm	225 +0/-5℃	225 +0/-5°C	



Table 6-3 Pb-free - Classification Temperature

Package	Volume mm³	Volume mm³	Volume mm³
Thickness	< 350	350 - 2000	> 2000
< 1.6mm	260℃	260℃	260℃
1.6 mm - 2.5mm	260℃	250℃	245℃
> 2.5mm	250℃	245℃	245℃

Note

1.*Tolerance The device manufacturer/supplier shall assure process compatibility up to and including the stated classification temperature (this means Peak reflow temperature +0 $^{\circ}$ C.For example 260 $^{\circ}$ C+0 $^{\circ}$ C)at the rated MSL level.

